

AF/2814



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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Scott G. Meikle et al.
Title: METHOD OF DEPOSITING TUNGSTEN NITRIDE USING A SOURCE GAS COMPRISING SILICON
Docket No.: 303.444US5
Filed: December 5, 2001
Examiner: Ginette Peralta
Serial No.: 10/004,714
Due Date: March 15, 2003 (Saturday)
Group Art Unit: 2814

Box AF

Commissioner for Patents
Washington, D.C. 20231

We are transmitting herewith the following attached items (as indicated with an "X"):

- ☒ A return postcard.
- ☒ A Response under 37 CFR § 1.116 (8 Pages).

Please consider this a **PETITION FOR EXTENSION OF TIME** for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Box AF, Commissioner for Patents, Washington, D.C. 20231, on this 17th day of March, 2003.

Name

Amy Moriarty

Signature

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Customer Number 21186

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
(GENERAL)

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EXPEDITED PROCEDURE - EXAMINING GROUP 2814

#7/Response(NE)
3.26.03
C Moore
PATENT

S/N 10/004714

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REMARKS

Applicant has carefully reviewed and considered the Office Action mailed on January 15, 2003.

§112 Rejection of the Claims

Claims 41-74 were rejected under 35 USC § 112, first paragraph. The rejections states:

... the specification, while being enabling for a tungsten nitride layer, does not reasonably provide enablement for a tungsten nitride layer that includes silicon. The specification does not enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make the invention commensurate in scope with these claims.

Applicant respectfully traverses, and respectfully asserts that the specification does enable a tungsten nitride layer that includes silicon. The tungsten nitride is chemically vapor deposited from a source gas comprising a silicon based gas (page 3 lines 9-10, page 5 lines 4-5). The specification identifies tungsten sources, nitrogen sources, and silicon sources for the source gas (page 6 lines 3-9). Additionally, the specification identifies pressures, temperatures and flow rates (page 6 line 9 to page 7 line 8). Applicant respectfully asserts that the disclosure in the present application enables one of ordinary skill in the art to make a tungsten nitride layer that includes silicon.